

74AUP1G19

Low-power 1-of-2 decoder/demultiplexer

Rev. 01 — 13 August 2008

Product data sheet

1. General description

The 74AUP1G19 provides a 1-of-2 decoder/demultiplexer with a common output enable. It buffers the data on input pin A and passes it either to output pin 1Y (true) or 2Y (complement), depending on whether the state of the enable input pin $\bar{E}$ is LOW or HIGH, respectively.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101-C exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40^{\circ}C$ to $+85^{\circ}C$ and $-40^{\circ}C$ to $+125^{\circ}C$

3. Ordering information

Table 1. Ordering information

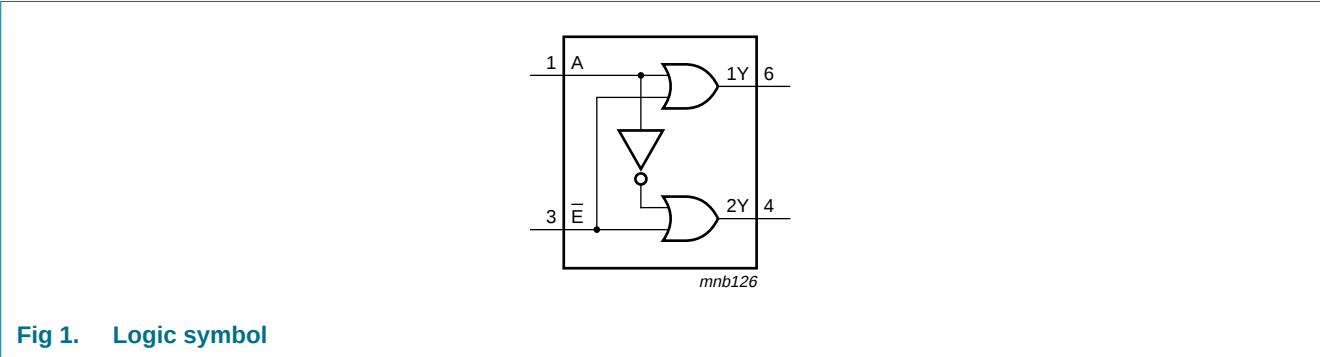
Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G19GW	−40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP1G19GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G19GF	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

4. Marking

Table 2. Marking

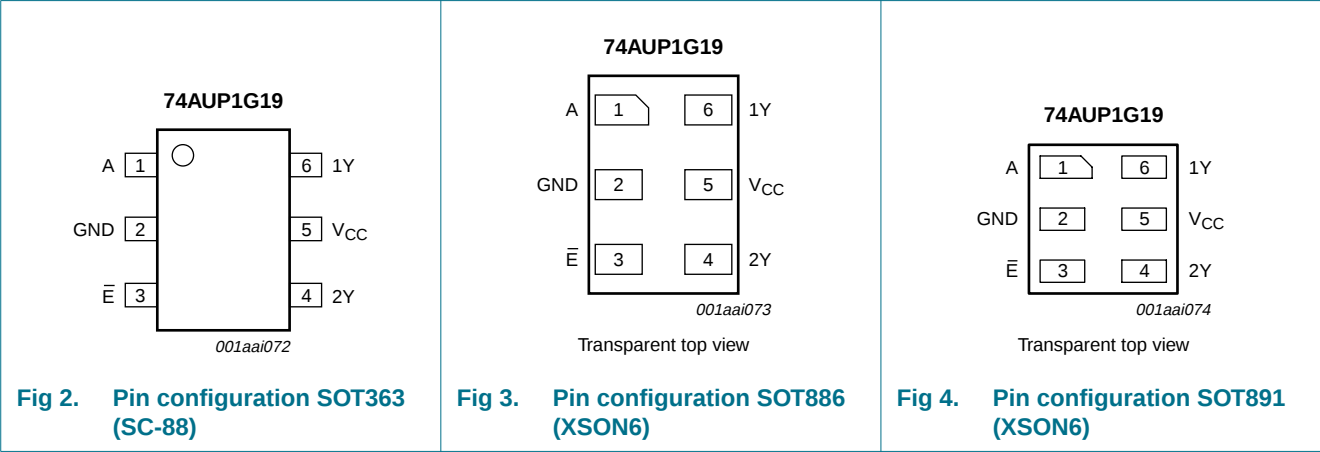
Type number	Marking code
74AUP1G19GW	pY
74AUP1G19GM	pY
74AUP1G19GF	pY

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
A	1	data input
GND	2	ground (0 V)
$\overline{E}$	3	enable input (active LOW)
2Y	4	data output (complement)
V _{CC}	5	supply voltage
1Y	6	data output (true)

7. Functional description

Table 4. Function table^[1]

Input		Output	
$\overline{E}$	A	1Y	2Y
L	L	L	H
L	H	H	L
H	L	H	H
H	H	H	H

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	± 50	mA
V_O	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	± 20	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1] -	-	40	µA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	0.8	-	pF
C _O	output capacitance	V _O = GND; V _{CC} = 0 V	-	1.7	-	pF

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.5	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1] -	-	50	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.75	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	1.4	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1]	-	75	µA

[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	

C_L = 5 pF

t _{pd}	propagation delay	A to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	15.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.3	5.3	11.5	2.1	11.9	12.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	3.8	6.8	2.0	7.5	7.8	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.1	5.4	1.5	6.1	6.4	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	2.3	4.0	1.2	4.2	4.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.0	3.4	1.0	3.8	4.1	ns
		$\bar{E}$ to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	17.8	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	5.8	11.6	2.1	12.0	12.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	4.2	6.9	1.9	7.5	7.8	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.4	5.6	1.5	6.2	6.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	2.6	4.0	1.3	4.5	4.8	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.2	3.4	1.2	3.7	3.9	ns

C_L = 10 pF

t _{pd}	propagation delay	A to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	18.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.5	6.2	13.8	2.5	13.9	14.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	4.5	8.2	2.1	8.5	8.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	3.7	6.3	2.0	6.8	7.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	2.9	4.7	1.6	5.0	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	2.6	4.0	1.4	4.4	4.7	ns
		$\bar{E}$ to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	21.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	6.7	13.4	2.5	13.9	14.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	4.8	8.2	2.1	8.8	9.1	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	4.0	6.4	1.9	7.0	7.3	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	3.1	4.7	1.6	5.1	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	2.8	4.2	1.4	4.4	4.7	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	

C_L = 15 pF

t _{pd}	propagation delay	A to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	21.8	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.0	7.0	15.2	2.7	15.8	16.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.0	9.0	2.5	9.8	10.2	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.2	7.0	2.2	7.8	8.2	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.4	5.3	1.9	5.6	6.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.9	3.0	4.6	1.7	5.2	5.4	ns
		$\bar{E}$ to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	24.2	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.0	7.5	15.1	2.8	15.7	16.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.4	9.1	2.5	10.0	10.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.5	7.2	2.2	8.0	8.4	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.6	5.4	2.0	5.8	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.9	3.2	4.7	1.8	5.1	5.4	ns

C_L = 30 pF

t _{pd}	propagation delay	A to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	30.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	9.2	20.5	3.6	21.3	21.7	ns
		V _{CC} = 1.4 V to 1.6 V	3.2	6.6	11.5	3.3	12.8	13.4	ns
		V _{CC} = 1.65 V to 1.95 V	3.1	5.5	9.5	3.0	10.0	10.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.9	4.6	6.3	2.6	7.2	7.7	ns
		V _{CC} = 3.0 V to 3.6 V	2.7	4.2	5.9	2.5	7.0	7.4	ns
		$\bar{E}$ to nY; see Figure 5	[2]						
		V _{CC} = 0.8 V	-	33.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	9.8	20.0	3.5	20.9	21.3	ns
		V _{CC} = 1.4 V to 1.6 V	3.2	7.0	11.6	3.3	12.8	13.5	ns
		V _{CC} = 1.65 V to 1.95 V	3.1	5.8	9.3	3.0	10.3	10.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.9	4.7	6.8	2.7	7.4	7.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.7	4.3	6.0	2.5	7.0	7.4	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

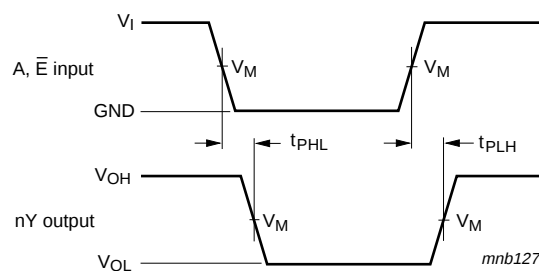
Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	

C_L = 5 pF, 10 pF, 15 pF and 30 pF

C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} ^[3]							
		V _{CC} = 0.8 V	-	5.8	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	5.9	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	5.9	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	6.0	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	6.8	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	7.7	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



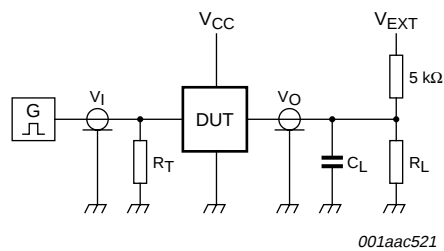
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 5. The data input (A or $\bar{E}$) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	V _I	t _r = t _f
0.8 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns



Test data is given in [Table 10](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 6. Load circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V_{EXT}
V_{CC}	C_L	R_L	t_{PLH} , t_{PHL}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	1 MΩ	open

13. Package outline

Plastic surface-mounted package; 6 leadsSOT363

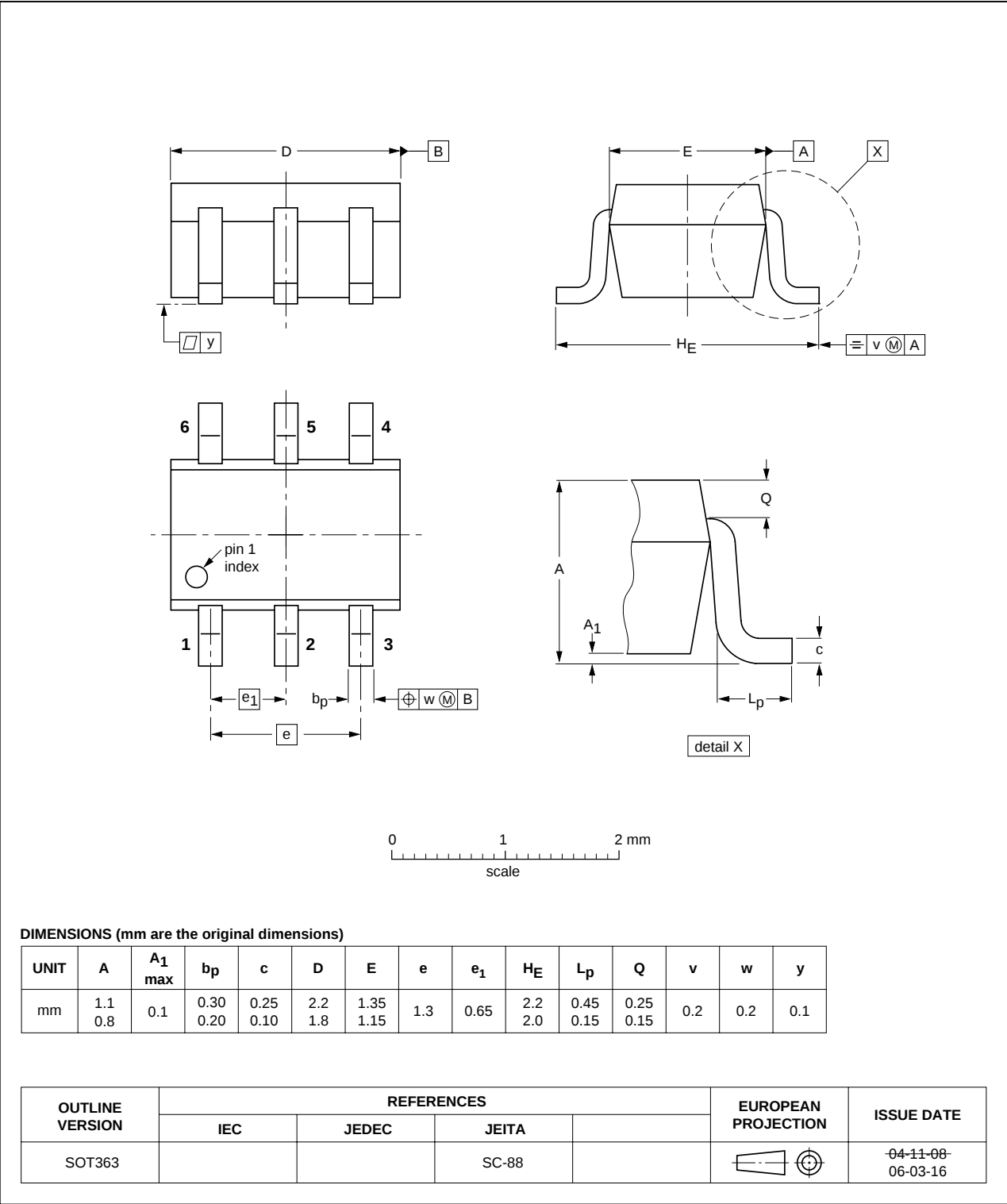


Fig 7. Package outline SOT363 (SC-88)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

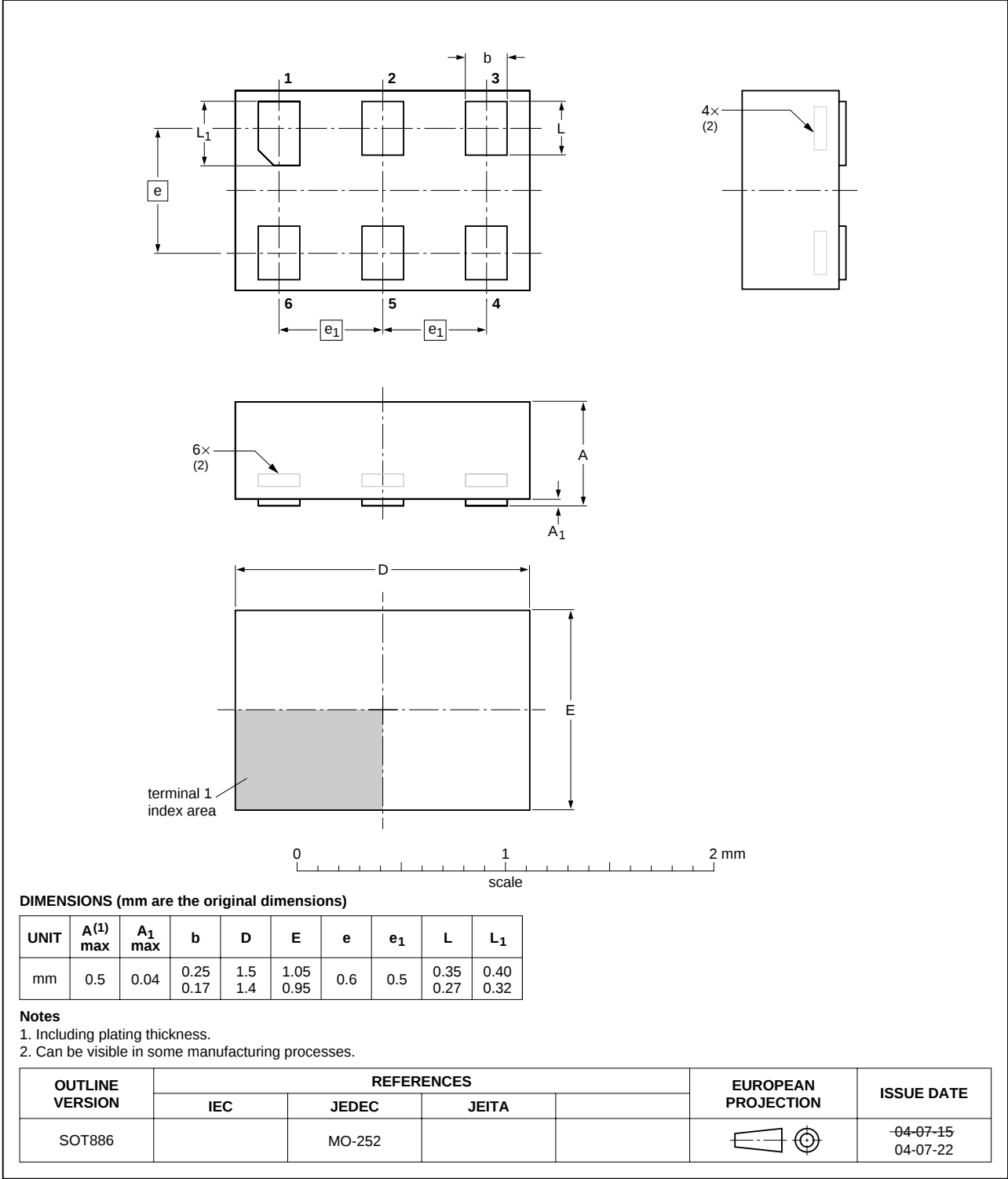


Fig 8. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

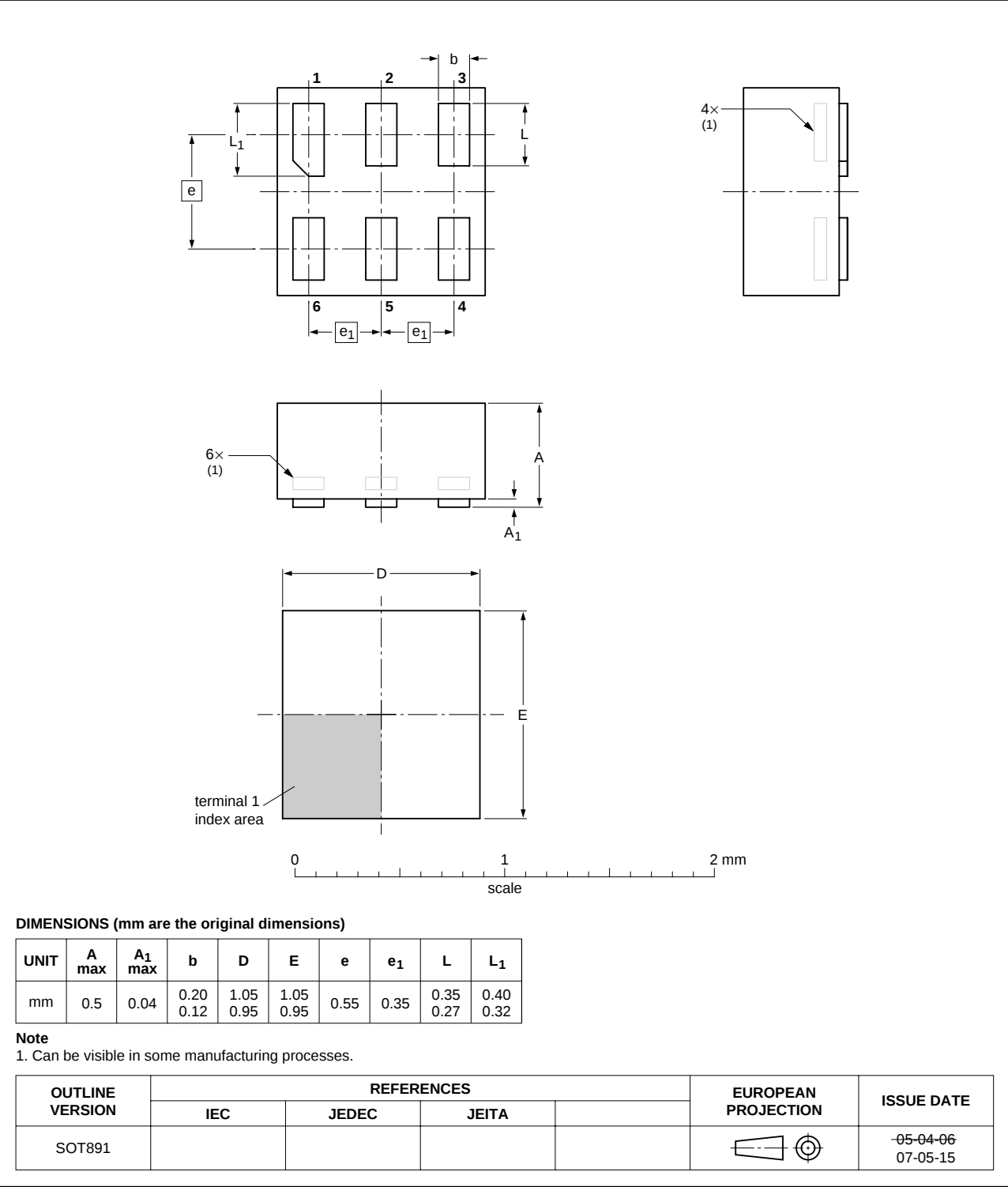


Fig 9. Package outline SOT891 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
TTL	Transistor Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
CDM	Charged Device Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G19_1	20080813	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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